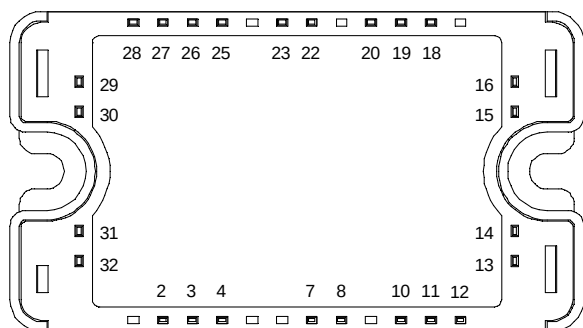
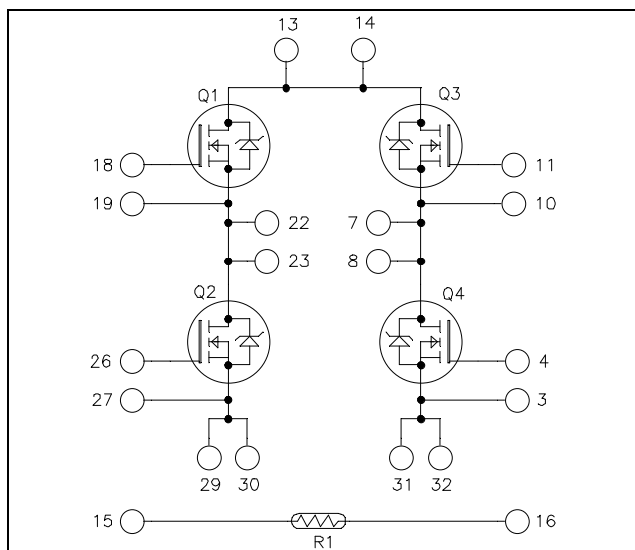


Full bridge MOSFET Power Module

$V_{DSS} = 1000V$

$R_{DSon} = 460m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 19A$ @ $T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together

Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8TM Fast FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
 - Symmetrical design
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	19
		$T_c = 80^\circ C$	14
I_{DM}	Pulsed Drain current	120	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	552	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	357
I_{AR}	Avalanche current (repetitive and non repetitive)	16	A



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 16\text{A}$		460	552	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		6800		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		715		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		92		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		260		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500\text{V}$		46		
Q_{gd}	Gate – Drain Charge	$I_D = 16\text{A}$		125		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 16\text{A}$ $R_G = 2.2\Omega$		36		ns
T_r	Rise Time			37		
$T_{d(off)}$	Turn-off Delay Time			140		
T_f	Fall Time			35		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			19	A
		$T_c = 80^\circ\text{C}$			14	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -16\text{A}$			1	V
dv/dt	Peak Diode Recovery ❶				25	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -16\text{A}$ $V_R = 100\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		290	ns
			$T_j = 125^\circ\text{C}$		600	
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	1.3		μC
			$T_j = 125^\circ\text{C}$	3.5		

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$I_S \leq -16\text{A}$ $di/dt \leq 1000\text{A}/\mu\text{s}$ $V_{DD} \leq 667\text{V}$ $T_j \leq 125^\circ\text{C}$

Thermal and package characteristics

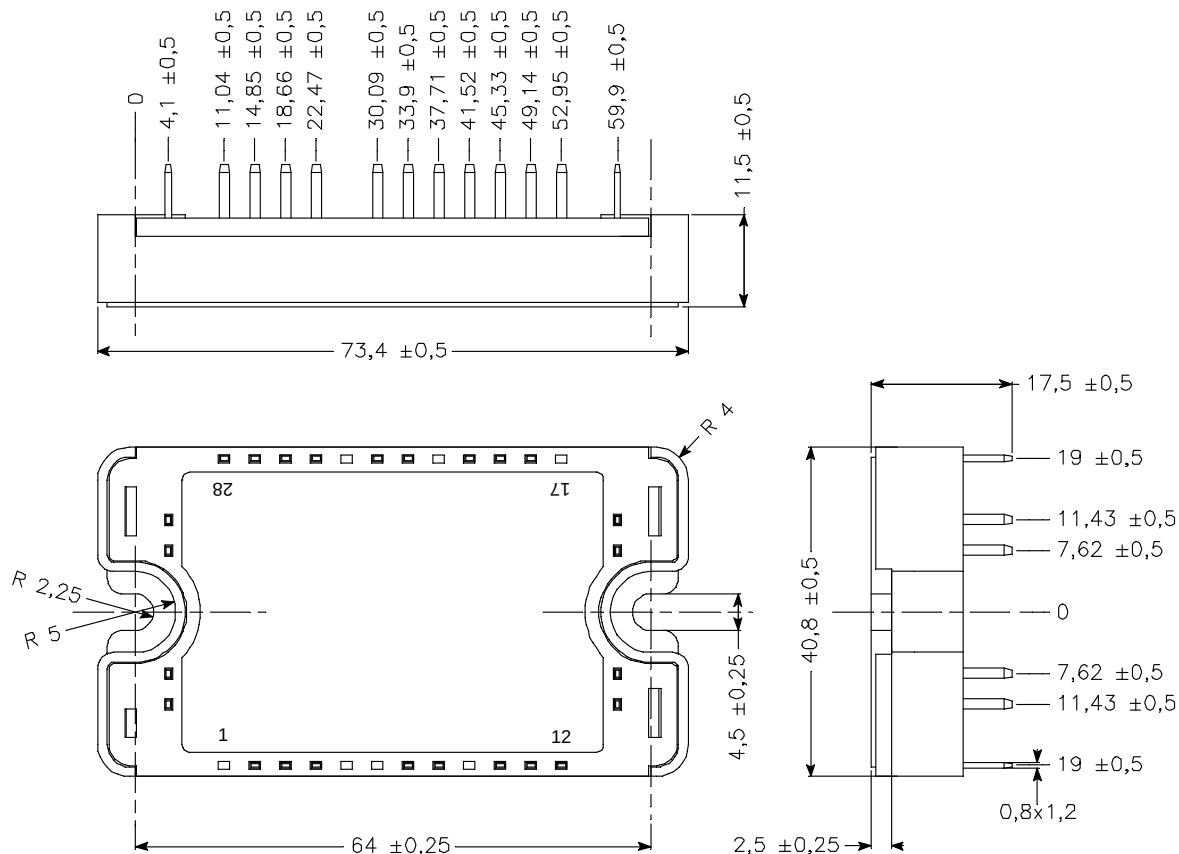
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.35	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

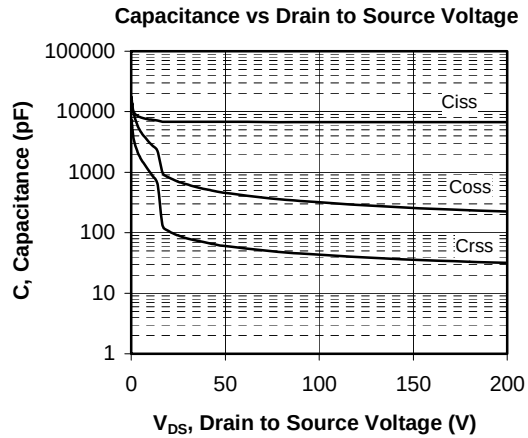
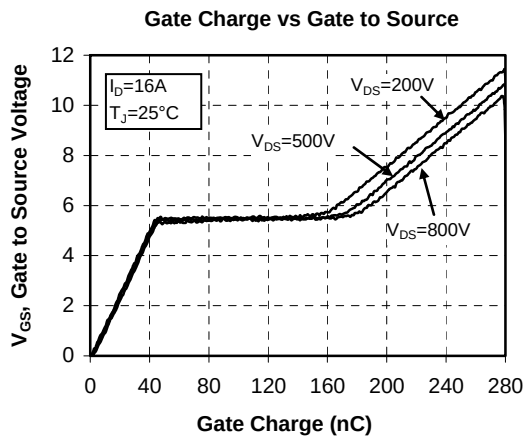
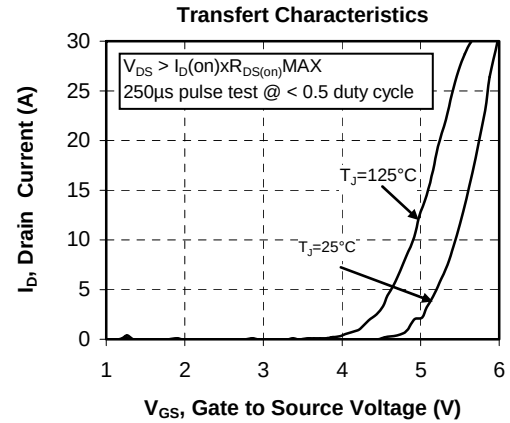
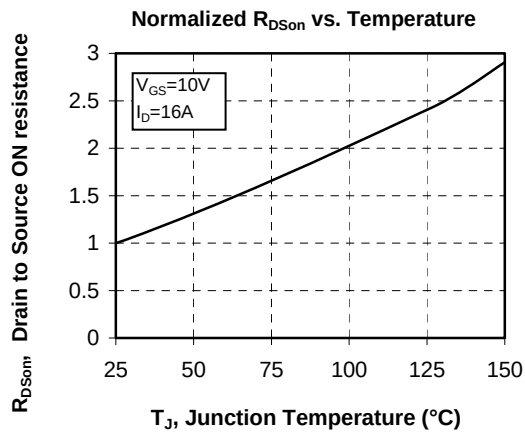
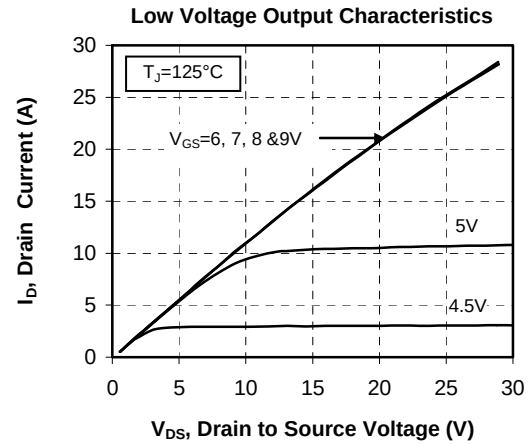
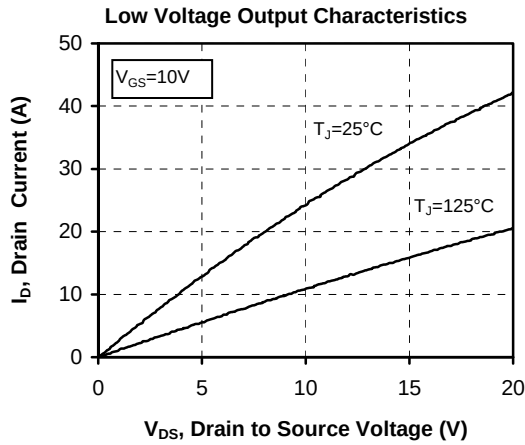
Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$			5		%
$B_{25/85}$	$T_{25} = 298.15$ K		3952		K
$\Delta B/B$	$T_C = 100^\circ\text{C}$		4		%

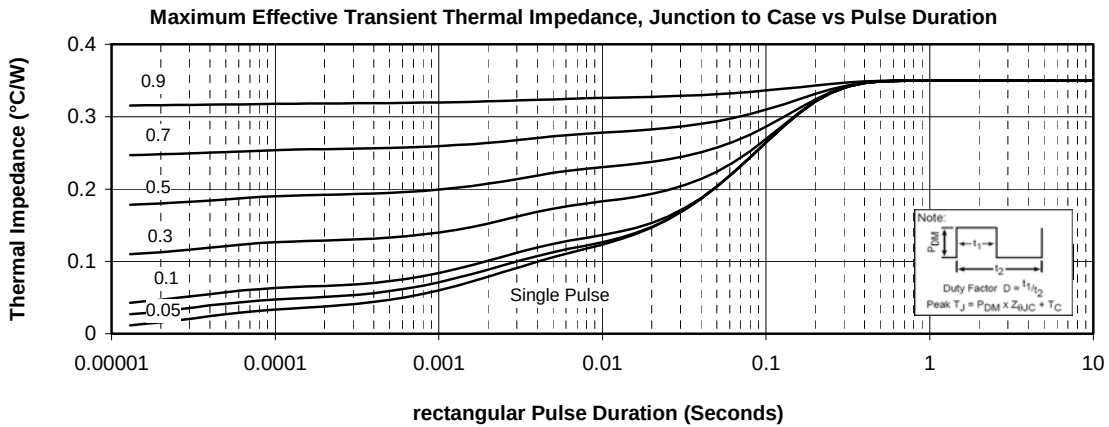
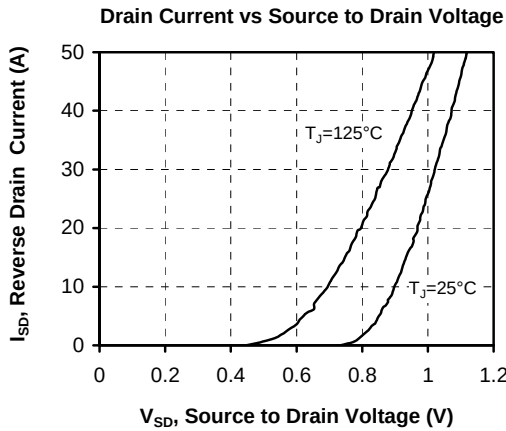
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T : Thermistor temperature
 R_T : Thermistor value at T

SP3 Package outline (dimensions in mm)

 See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.